





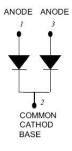
306CNQ200 SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- · Center tap module
- High purity, high temperature epoxy encapsulation for
- · enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V	
Average Rectified Forward Current	Bootified Forward Current 50% duty cycle @Tc		150(Per Leg)	Α	
Average Rectilled Forward Current	I _F (AV)	rectangular wave form	300(Per Device)	Α.	
Peak One Cycle Non-Repetitive		8.3 ms, half Sine pulse	3840	Α	
Surge Current (Per Leg)	I _{FSM}		00+0	, ,	

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •







Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 150A, Pulse, T _J = 25 °C @ 300A, Pulse, T _J = 25 °C	0.84 -	0.86 1.03	V
	V_{F2}	@ 150A, Pulse, T _J = 125 °C @ 300A, Pulse, T _J = 125 °C	0.71 -	0.76 0.86	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ}\text{C}$	0.0001	10	mA
	I _{R2}	$@V_R = \text{rated } V_{R,} T_J = 125 ^{\circ}\text{C}$	0.8	90	mA
Junction Capacitance(Per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	2300	3500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	cation	Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case(Per leg)	$R_{ heta JC}$	DC operation	0.4	10	°C/W
Typical Thermal Resistance Junction to Case(Per package)	$R_{ heta JC}$	DC operation	0.2	20	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.1	10	°C/W
Mounting Torque	T _M		Mounting Torque	24(min) 35(max)	Ka am
Mounting Torque	IM	-	Terminal Torque	35(min) 46(max)	- Kg-cm
Approximate Weight	wt	-	79 g		g
Case Style	PRM4 Non-Isolated				



0.0

0.2

0.4

Forward Voltage Drop - V_F(V)

0.6

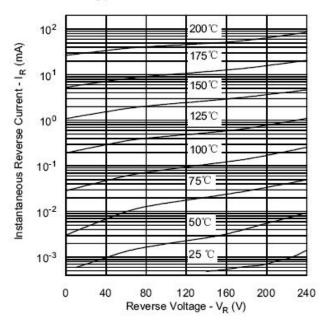




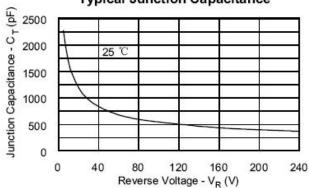
Ratings and Characteristics Curves

Typical Forward Characteristics 102 200°C 175°C 175°C 125°C 100¹ 100¹ 100¹

Typical Reverse Characteristics



Typical Junction Capacitance



1.0

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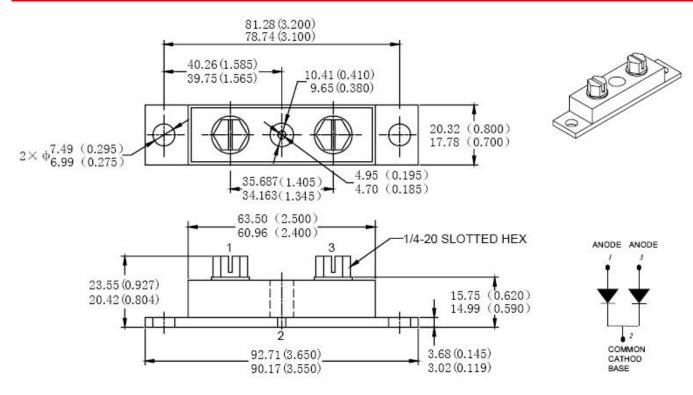
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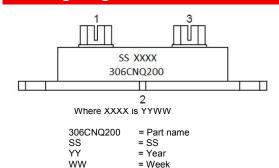




Mechanical Dimensions PRM4 Non-Isolated(Millimeters/Inches)



Marking Diagram



Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
306CNQ200	PRM4(Non- Isolated) (Pb-Free)	9 pcs/box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.









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